

## GRK-Workshop

„Nanoschichtstrukturen zur Funktionalisierung von Silizium“

Mittwoch, 10.01.2018, ab 14 st Uhr, Seminarraum 02D36 WZMW

<u>Date</u>	<u>Presenter</u>	<u>Topic</u>
14:00		Welcome and overview
14:05	P. Ludewig	MOVPE studies of Ga(NAs(Sb))-MQWH on Si
14:25	F. Pieck	Reaction dynamics in the growth of GaP
14:45	L. Ostheim	Electrical transport on GaP-on-Si-templates
15:05	S. Gupta	STEM-investigations on Ga(NAs)-MQWH on Si
15:25	A. Bäumner	Parameter studies on the material gain in Ga(NAsP)-MQWH on Si-substrate
15:45	Coffee break	Discussions
16:15	S. Gies	Band offset in Ga(NAsP)/GaP heterostructures
16:35	F. Dobener	Band offset at the Ga(N,As,P)/GaP Heterointerface
16:55	M. Stein	Studies for the dynamic material gain of Ga(NAsP)-MQWH on Si
17:15	V. Valkovskii	Rethinking the theoretical description of photoluminescence in compound semiconductors